

CMOSH2-4L  
 SURFACE MOUNT  
 HIGH CURRENT, LOW  $V_F$   
 SILICON SCHOTTKY DIODE

ULTRAm<sup>TM</sup>



SOD-523 CASE

**Central**<sup>TM</sup>  
 Semiconductor Corp.

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CMOSH2-4L is a high current, low  $V_F$  silicon Schottky diode in an SOD-523 surface mount package. This device offers a  $V_F$  as low as 0.33 volts and is designed for small signal general purpose applications where size and low loss is required.

**MARKING CODE: 4L**

**MAXIMUM RATINGS:** ( $T_A=25^\circ\text{C}$ )

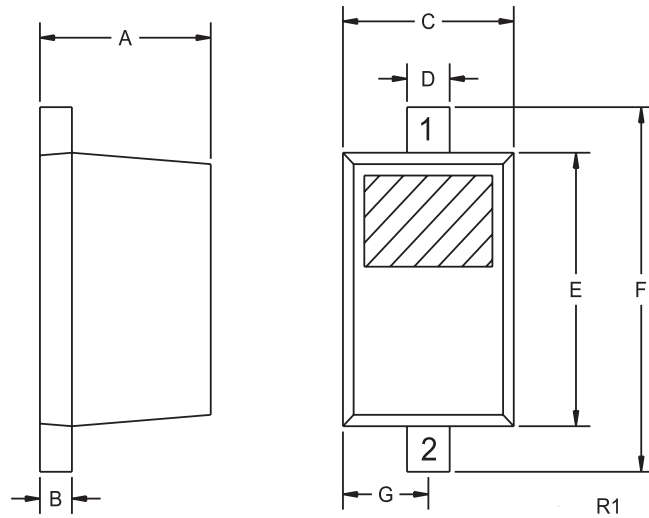
	SYMBOL		UNITS
Peak Repetitive Reverse Voltage	$V_{RRM}$	40	V
Continuous Forward Current	$I_F$	200	mA
Peak Repetitive Forward Current	$I_{FRM}$	350	mA
Forward Surge Current, $t_p=10\text{ms}$	$I_{FSM}$	1.0	A
Power Dissipation	$P_D$	250	mW
Operating and Storage			
Junction Temperature	$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$
Thermal Resistance	$\theta_{JA}$	500	$^\circ\text{C/W}$

**ELECTRICAL CHARACTERISTICS:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
$I_R$	$V_R=20\text{V}$		11	50	$\mu\text{A}$
$BV_R$	$I_R=100\mu\text{A}$	40	53		V
$V_F$	$I_F=10\text{mA}$		0.24	0.325	V
$V_F$	$I_F=100\text{mA}$		0.35	0.4	V
$V_F$	$I_F=200\text{mA}$		0.42	0.5	V
$C_T$	$V_R=4.0\text{V}, f=1.0\text{MHz}$		8.5	10	pF
$t_{rr}$	$I_F=I_R=10\text{mA}, I_{rr}=1.0\text{mA}, R_L=100\Omega$		4.0	5.0	ns

R2 (17-September 2004)

SOD-523 CASE - MECHANICAL OUTLINE



LEAD CODE:

- 1) Cathode
- 2) Anode

MARKING CODE: 4L

DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.020	0.031	0.50	0.80
B	0.004	0.008	0.10	0.20
C	0.028	0.035	0.70	0.90
D	0.008	0.011	0.20	0.28
E	0.039	0.055	1.00	1.40
F	0.055	0.071	1.40	1.80
G	0.016		0.40	

SOD-523 (REV: R1)